



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D Τ _A = 25°C
20V	$48mΩ @ V_{GS} = 4.5V$	2.8A
200	59mΩ @ V _{GS} = 2.5V	2.6A

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions

Benefit and Features

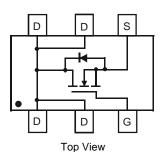
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.006 grams (approximate)



Top View



Internal Schematic

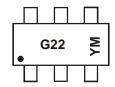
Ordering Information (Note 3)

Ī	Part Number	Case	Packaging
	DMN2075UDW-7	SOT363	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com
- 3. For packaging details, go to our website at http://www.diodes.com

Marking Information



G22 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α	E	3	С		D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	20	V		
Gate-Source Voltage			V_{GSS}	±8V	V
Continuous Drain Current (Note 5) V 4.5V	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I _D	2.8 2.2	А
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t<5s	$T_A = 25$ °C $T_A = 70$ °C	I _D	3.1 2.5	А
Continuous Drain Current (Note 5) V 25V	I _D	2.6 2.1	Α		
Continuous Drain Current (Note 5) V _{GS} = 2.5V	I _D	2.8 2.2	А		
Pulsed Drain Current (10µs pulse, Duty cycle = 1%)	I _{DM}	20	Α		
Maximum Continuous Body Diode Current	I _S	1.0	Α		

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 4)		P_{D}	0.5	W
Thermal Resistance, Junction to Ambient (Note 4)	Steady state	ר	257	°C/W
L Thermal Resistance, Junction to Ambient (Note 4)	t<5s	$R_{\theta JA}$	213	°C/W
Total Power Dissipation (Note 5)		P_D	0.58	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	ס	221	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{ heta JA}$	183	°C/W
Thermal Resistance, Junction to Case (Note 5)		$R_{ heta JC}$	65	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

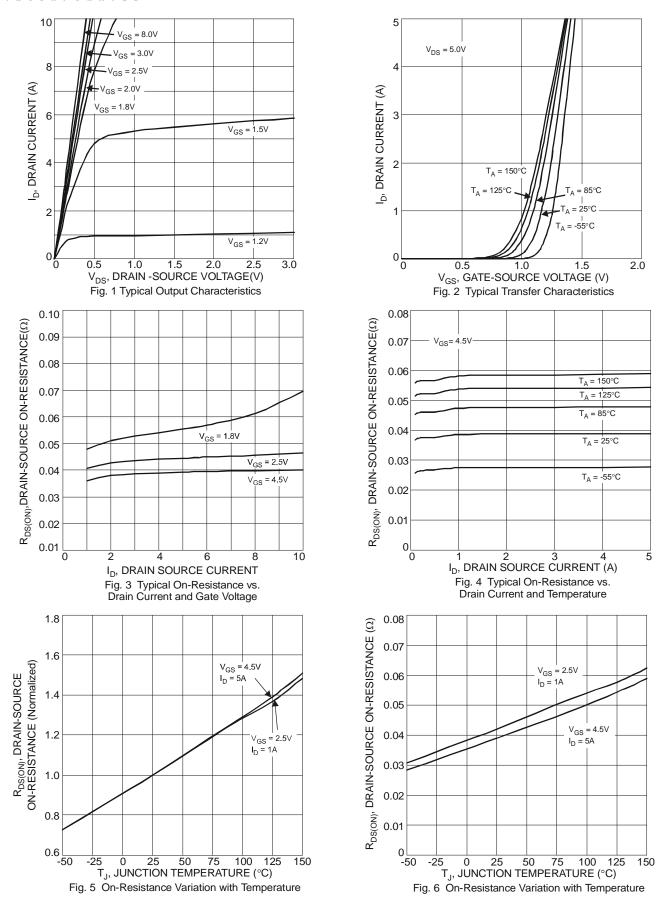
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(th)}$	0.4	-	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		-	40	48	_	$V_{GS} = 4.5V, I_D = 3A$	
Ctatia Dania Course On Registeres		-	45	59	$m\Omega$	$V_{GS} = 2.5V, I_D = 2A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	-	51	70	11177	V _{GS} = 1.8V, I _D = 1A	
		-	68	100		$V_{GS} = 1.5V, I_D = 1A$	
Forward Transfer Admittance	Y _{fs}	-	13	-	S	$V_{DS} = 5V, I_{D} = 3A$	
Diode Forward Voltage	V _{SD}	-	0.75	1.0	V	V _{GS} = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 6)	•						
Input Capacitance	C _{iss}	ı	594.3	-	pF	101/11/	
Output Capacitance	Coss	-	64.5	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	57.7	-	pF	-1 = 1.0WHZ	
Gate Resistance	Rg	-	1.5	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	-	7.0	-	nC	4.5)/.)/ 4.0)/	
Gate-Source Charge	Q _{gs}	-	0.9	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q _{gd}	-	1.4	-	nC	I _D = 3.6A	
Turn-On Delay Time	t _{D(on)}	-	7.4	-	ns		
Turn-On Rise Time	tr	-	9.8	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	28.1	-	ns	$R_L = 2.78\Omega, R_G = 1.0\Omega$	
Turn-Off Fall Time	t _f	-	6.7	-	ns		

Notes:

- 4. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
- 6. Short duration pulse test used to minimize self-heating effect
- 7. Guaranteed by design. Not subject to production testing.







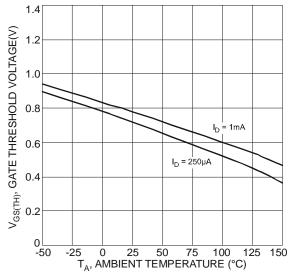
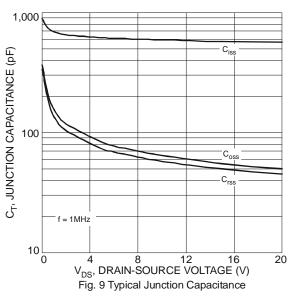
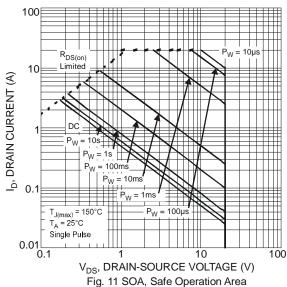
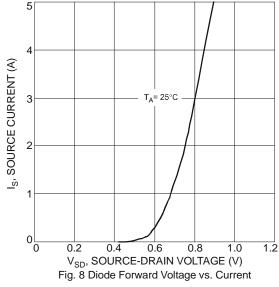


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







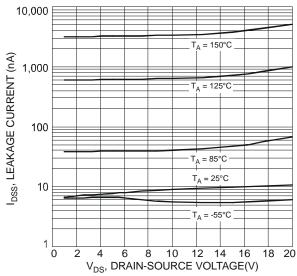
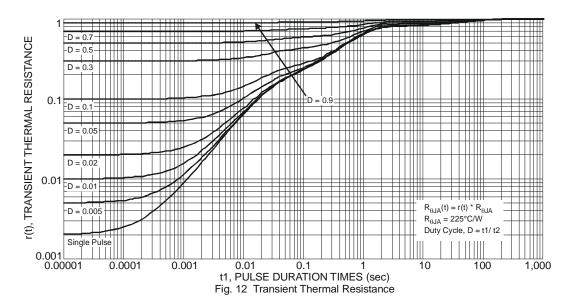
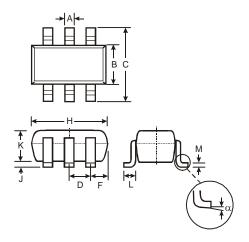


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage



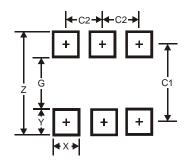


Package Outline Dimensions



SOT363							
Dim	Min Max						
Α	0.10	0.30					
В	1.15	1.35					
С	2.00	2.20					
D	0.65	Тур					
F	0.40	0.45					
Н	1.80	2.20					
J	0 0.10						
K	0.90 1.00						
L	L 0.25 0.40						
M	0.10 0.22						
α	0°	8°					
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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